

## REMARKS/ARGUMENT

The applicants' attorneys appreciate the Examiner's thorough search and remarks.

Responsive to the objections set forth in paragraph 3 of the Office Action, numeral 5 identifies a line along which a cross-section is taken in Figure 4, numeral 4 identifies a line in Figure 5 along which a cross-section is taken, numeral 10 identifies a line in Figure 9 along which a cross-section is taken, and numeral 12 identifies a line in Figure 11 along which a cross-section is taken. The Examiner is referred to paragraphs 9, 10, 14 and 15 of the substitute specification attached hereto where the foregoing numerals are discussed. Withdrawal of the objection is requested.

Responsive to paragraph 4 of the Office Action, sinker 60 has been changed to drain 60. Withdrawal of the objection is requested.

Responsive to the objection set forth in paragraph 5 of the Office Action, the title of the application has been changed to "Lateral Conduction Superjunction Semiconductor Device." Withdrawal of the objection is requested.

Claim 1 has been rejected under 35 U.S.C. §103(a) as obvious over Kitamura et al., U.S. Patent No. 5,844,275 in view of Ranjan, U.S. Patent No. 5,861,657 and in further view of Sakakibara et al., U.S. Patent No. 5,449,946. Reconsideration is requested.

Claim 1 calls for, in combination with other limitations, a plurality of trenches defining mesas, a drain region and a MOSgate structure, "wherein each of said mesas extends between said drain region and said MOSgate structure." Kitamura et al. show a semiconductor device having a drain region, a MOSgate structure and a trench disposed between the drain region and the MOSgate structure. The trench region shown by Kitamura et al. is oriented such that its long axis (the axis that extends between its ends parallel to the vertical sidewalls of the trench) does not extend between its drain region and the MOSgate structure. Consequently, the mesas defined by the trench in the device of Kitamura et al. do not extend between the drain and the MOSgate structure. Reconsideration of claim 1 is requested.

Claims 2-28 depend from claim 1, and, therefore, include at least its limitations.

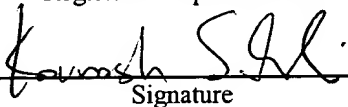
Each of these claims includes other limitations, which in combination with those of claim 1 are not shown or suggested by the art of record. Reconsideration is requested.

The application is believed to be in condition for allowance. Such action is earnestly solicited.

I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Asst. Commissioner for Patents, Washington, D.C. 20231, on October 31, 2002:

Kourosh Salehi

Name of applicant, assignee or  
Registered Representative

  
Signature

October 31, 2002

Date of Signature

Respectfully submitted,



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